



Product Summary

BV _{DSS}	- 12 V
R _{DS(ON)}	50mΩ
I _D	- 4.3A

Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Circuit diagram

Package and Pin Configuration

SOT-23



Marking: 1F Or F1TPM

"TPM"= TECH PUBLIC Mosfet

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		-12	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Continuous Drain Current	T _A = 25°C	-4.3	A
I _{DM}	Pulsed Drain Current note1		-13	A
P _D	Power Dissipation	T _A = 25°C	1.3	W
R _{θJA}	Thermal Resistance, Junction to Ambient		150	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C



Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}= -250\mu\text{A}$	-12	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = -20\text{V}, V_{\text{GS}} = 0\text{V},$	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$	-0.4	-	-0.95	V
$R_{\text{DS}(\text{on})}$ note2	Static Drain-Source on-Resistance	$V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -4.3\text{A}$	-	-	50	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_{\text{D}} = -2.5\text{A}$	-	-	85	
V_{SD}	Drain to Source Diode Forward Voltage				-1.2	V
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}} = -10\text{V}, V_{\text{GS}} = 0\text{V},$ $f = 1\text{ MHZ}$	-	830	-	pF
C_{oss}	Output Capacitance		-	180	-	pF
Switching Characteristics						
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$(V_{\text{DS}} = 5\text{V}, V_{\text{GS}} = 4.5\text{V}, R_{\text{GEN}} = 6\Omega)$	-	11	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	250	-	ns

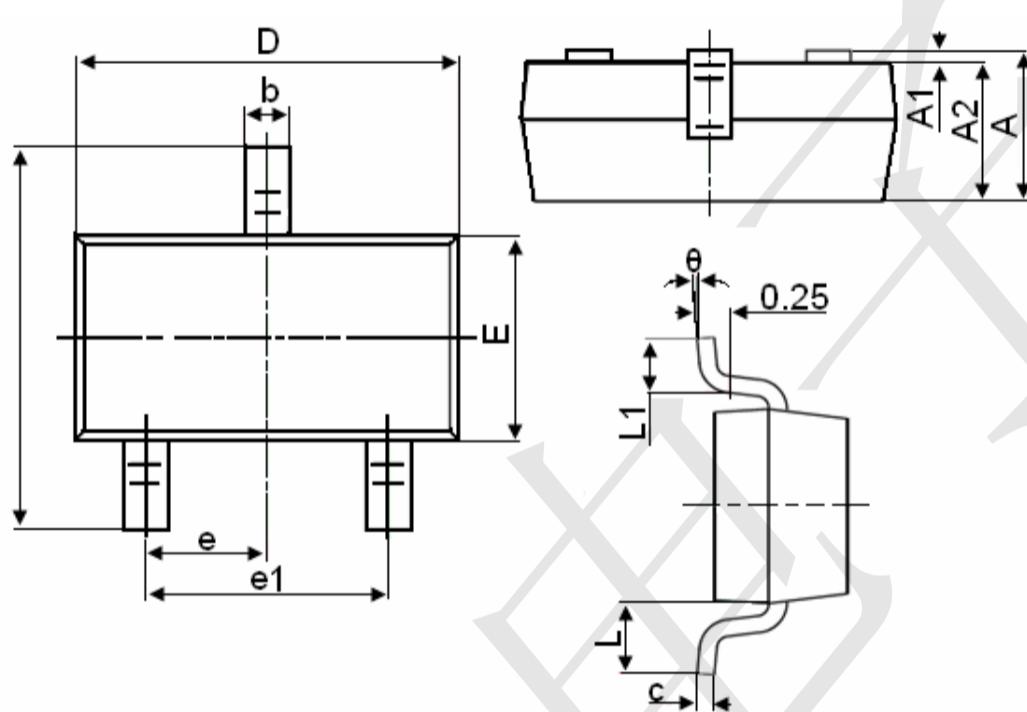


TECH PUBLIC
台舟电子

IRLML6401TRPBF
-12V P-Channel MOSFET

www.sot23.com.tw

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°